

IN THE CLAIMS

Please amend the claims as follows:

1-10. (Canceled)

11. (Previously presented) An epitaxial growth method comprising:

growing an epitaxial layer on a layered substrate,

wherein the layered substrate comprises sapphire on silicon and the epitaxial layer comprises group III nitrides which exhibits bowing so as to reduce said bowing, wherein the layered substrate has at least two layers, wherein at least two of the layers have different thermal coefficients and have the same growth temperature.

12-23. (Canceled)

24. (Previously presented) The epitaxial growth method of claim 11 further comprising the step of removing the layered substrate after growing the epitaxial layer.

25. (Previously presented) The epitaxial growth method of claim 24 wherein the step of removing comprises mechanical polishing.

26. (Previously presented) The epitaxial growth method of claim 11 wherein a process of forming said layered substrate includes a heating step, wherein said layered substrate exhibits the bowing after being cooled down from said heating step.

27. (Canceled)

28. (New) The epitaxial growth method of claim 11, wherein the thickness of the silicon is less than 6 microns, the thickness of the epitaxial layer is less than 3 microns and the wafer bowing is less than 0.5 m^{-1} .

29. (New) The epitaxial growth method of claim 11, wherein the thickness of the silicon is from 2 to 10 microns, the thickness of the epitaxial layer is from 3 to 10 microns and the wafer bowing is less than 0.5 m^{-1} .

30. (New) The epitaxial growth method of claim 11, wherein the thickness of the silicon is from 20 to 30 microns, the thickness of the epitaxial layer is from 40 to 60 microns and the wafer bowing is less than 0.5 m^{-1} .